

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT223 surface mountable plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- High immunity to false turn-on by  $dV/dt$
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

## 3. Applications

- General purpose motor control
- Small loads in washing machines
- Solenoid drivers

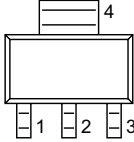
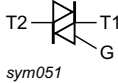
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DRM}$	repetitive peak off-state voltage			800			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 115\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		2			A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>		17			A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$		18.7			A
$T_j$	operating junction temperature			-40 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		1	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		1	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		1	-	10	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>		-	-	12	mA
$V_T$	on-state voltage	$I_T = 2.0\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>		-	1.35	1.55	V

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
4	T2	main terminal 2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA302W-800ET	SOT223	BTA302W-800ETF	Reel	4000	SOT223	16-Mar-2006

## 7. Marking

Table 4. Marking codes

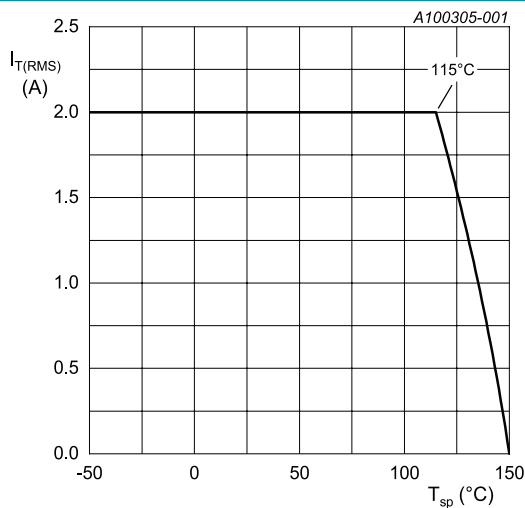
Type number	Marking codes	
	Assembly factory: d	Assembly factory: L
BTA302W-800ET	Jdxxx 302W8E	JLxxx 302W8E

## 8. Limiting values

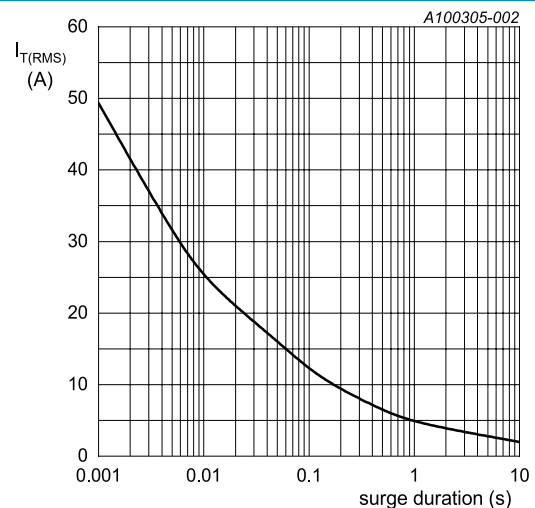
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage			800	V
$V_{RRM}$	repetitive peak reverse voltage			800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 115\text{ }^{\circ}\text{C}$ ; <a href="#">Fig 1</a> ; <a href="#">Fig 2</a> ; <a href="#">Fig 3</a>		2	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(imit)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>		17	A
		full sine wave; $T_{j(imit)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$		18.7	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN		1.4	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 20\text{ mA}$		100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current			2	A
$P_{GM}$	peak gate power			5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		0.1	W
$T_{stg}$	storage temperature			-40 to 150	$^{\circ}\text{C}$
$T_j$	operating junction temperature			-40 to 150	$^{\circ}\text{C}$



**Fig. 1. RMS on-state current as a function of solder point temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{sp} = 115\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

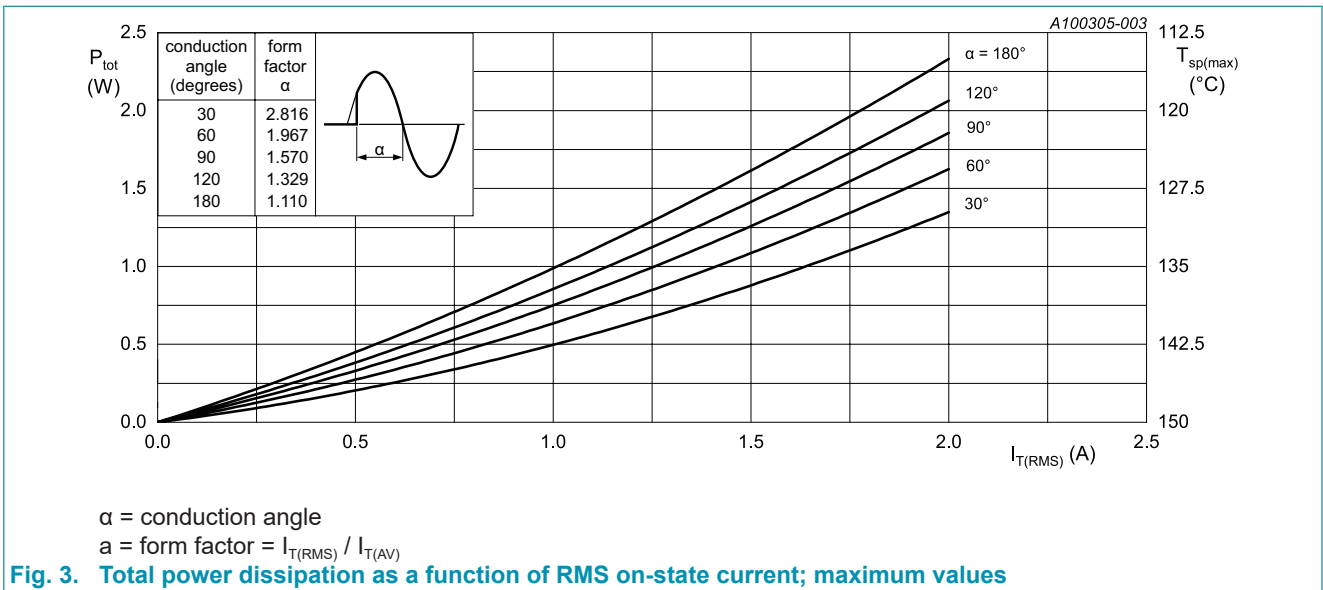


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

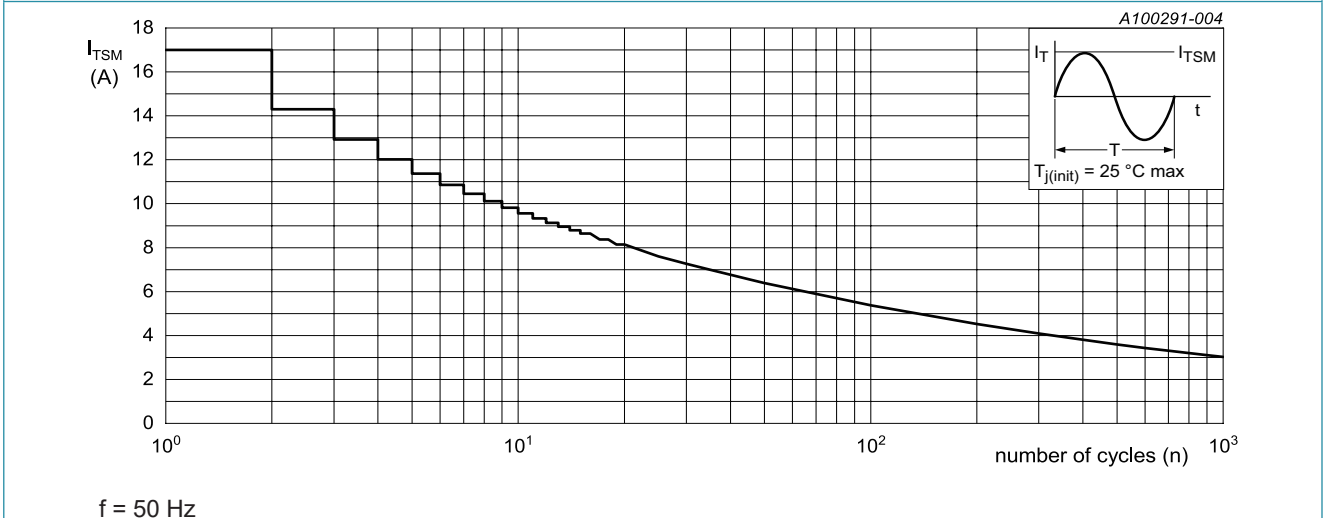


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

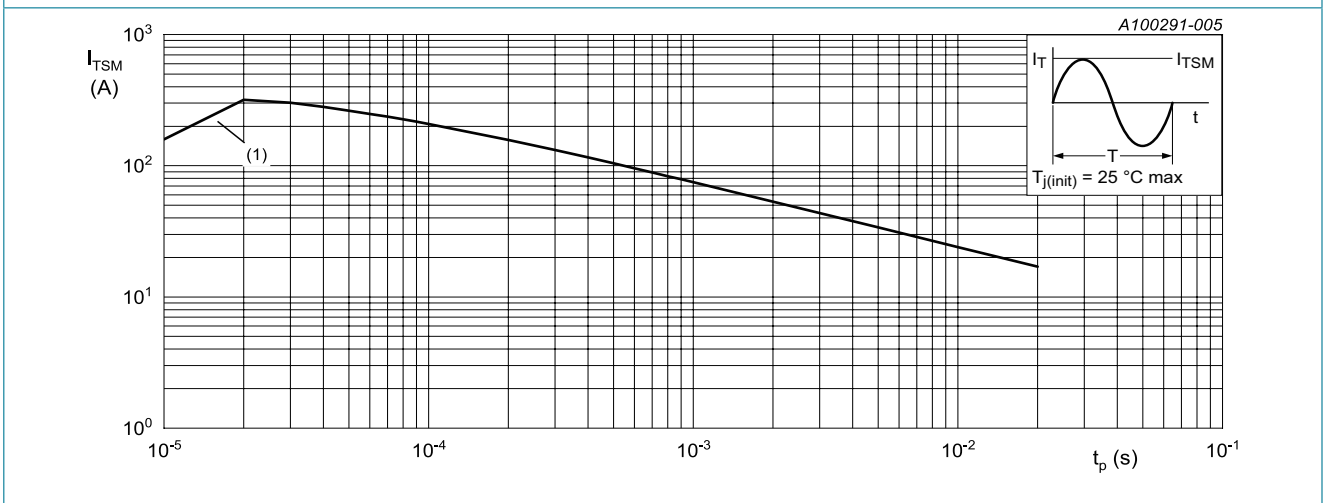


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; <a href="#">Fig 6</a>		-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; minimum footprint; <a href="#">Fig 7</a>		-	156	-	K/W
		in free air; printed-circuit board mounted; pad area; <a href="#">Fig 8</a>		-	70	-	K/W

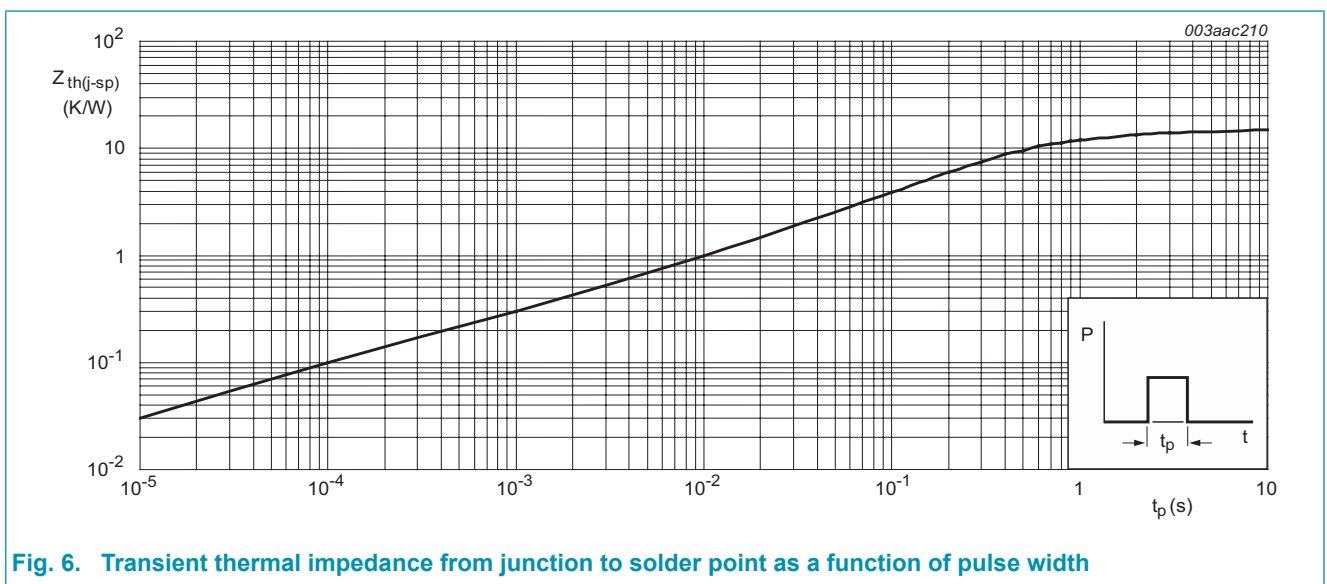
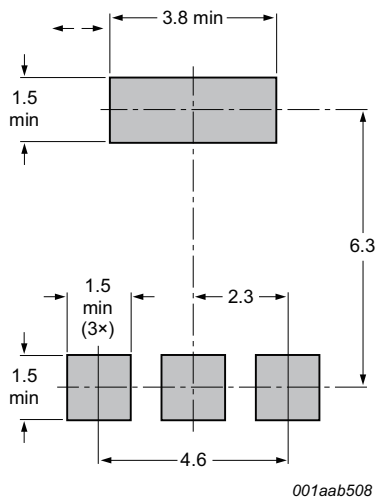


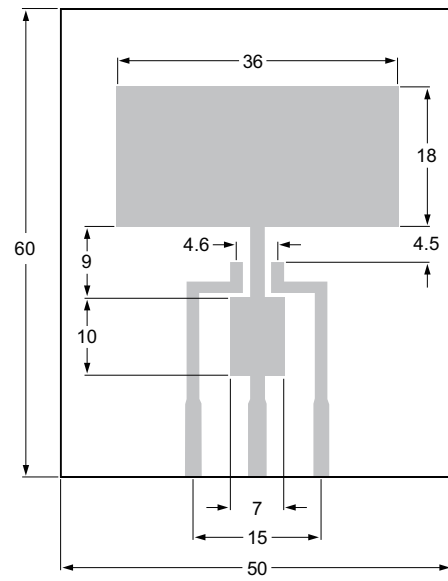
Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



001aab508

All dimensions are in mm

**Fig. 7. Minimum footprint SOT223**



001aab509

All dimensions are in mm

Printed circuit board:

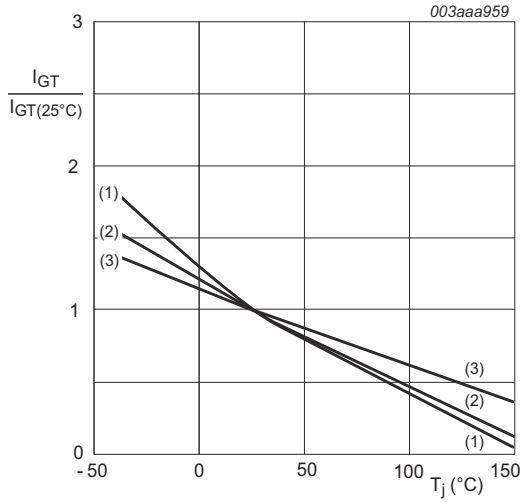
FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

**Fig. 8. Printed circuit board pad area: SOT223**

## 10. Characteristics

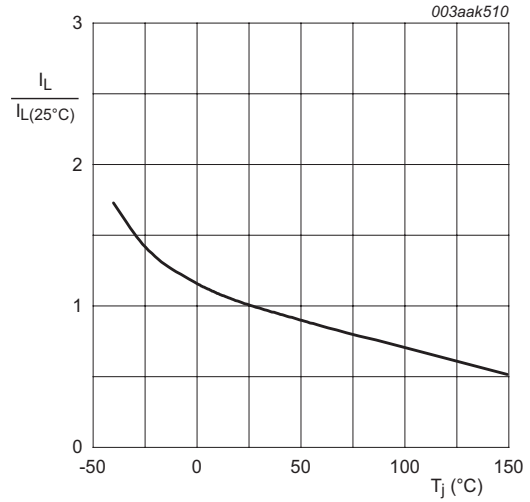
Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		1	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		1	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		1	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>		-	-	12	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>		-	-	20	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>		-	-	12	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 11</a>		-	-	12	mA
$V_T$	on-state voltage	$I_T = 2.0\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 12</a>		-	1.35	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 13</a>		-	0.7	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 125\text{ °C}$		0.2	0.3	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_J = 150\text{ °C}$		-	-	2	mA
$I_R$	reverse current	$V_R = 800\text{ V}$ ; $T_J = 150\text{ °C}$		-	-	2	mA
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		600	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_J = 125\text{ °C}$ ; $I_{T(RMS)} = 1.0\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit		2.5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_J = 125\text{ °C}$ ; $I_{T(RMS)} = 1.0\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit		3.5	-	-	A/ms

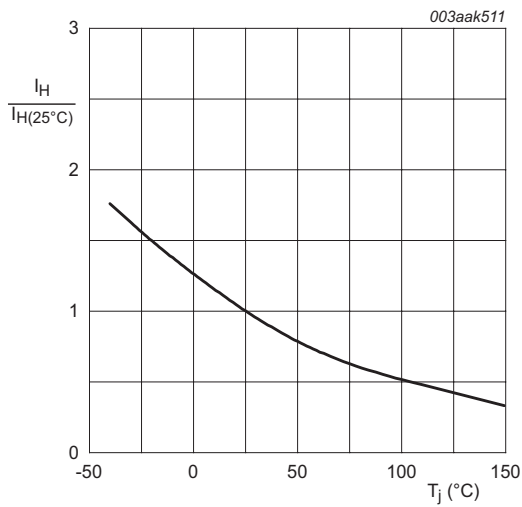


- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

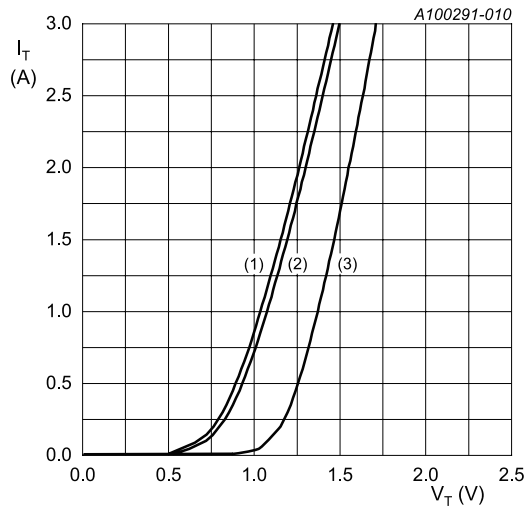
**Fig. 9. Normalized gate trigger current as a function of junction temperature**



**Fig. 10. Normalized latching current as a function of junction temperature**



**Fig. 11. Normalized holding current as a function of junction temperature**



- $V_o = 0.900 \text{ V}; R_s = 0.1775 \Omega$
- (1)  $T_j = 150^{\circ}\text{C}$ ; typical values
  - (2)  $T_j = 150^{\circ}\text{C}$ ; maximum values
  - (3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

**Fig. 12. On-state current as a function of on-state voltage**



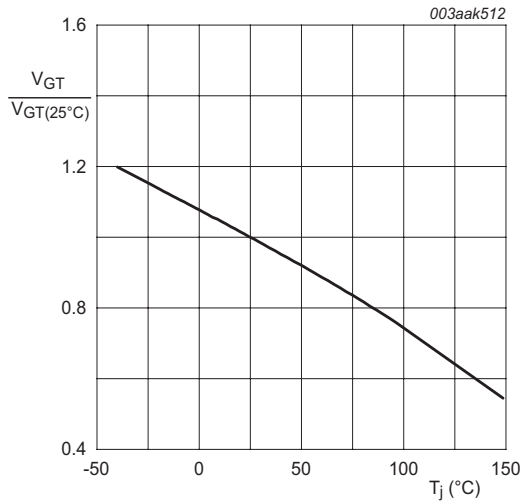
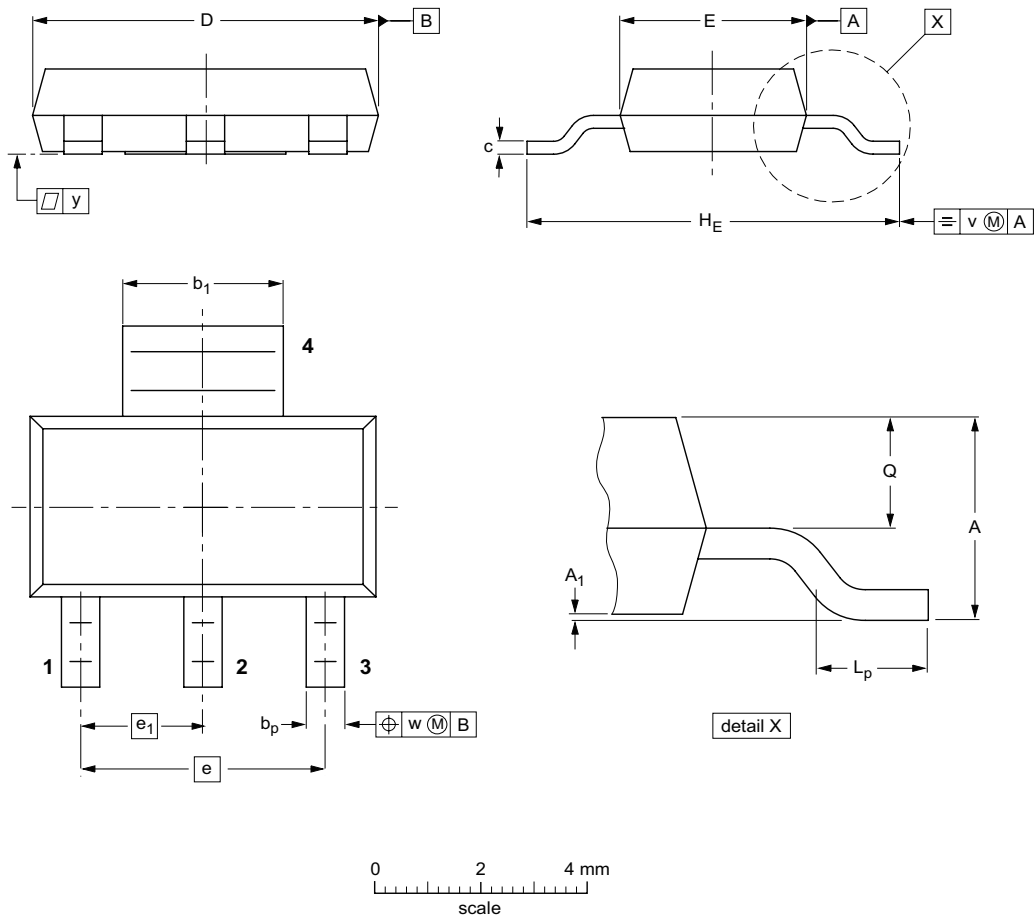


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

### 11. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			04-11-10 06-03-16

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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